Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V	
V_{GS}	gate-source voltage			-8	-	8	V	
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	800	mA	
Static characte	Static characteristics (per transistor)							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 500 \text{ mA}; T_j = 25 \text{ °C}$		-	290	380	mΩ	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	0 5 4	D1 D2
2	G1	gate TR1	6 5 4	
3	D2	drain TR2		G_1 A
4	S2	source TR2		
5	G2	gate TR2	1 2 3	
6	D1	drain TR1	SOT666	S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMDT290UNE	SOT666	plastic, surface-mounted package; 6 leads; 0.5 mm pitch; 1.6 mm x 1.2 mm x 0.55 mm body	SOT666		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMDT290UNE	AE

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or					
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	800	mA
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	500	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	3.2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	330	mW
			[1]	-	390	mW
		T _{sp} = 25 °C		-	1090	mW
Per device						
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	500	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode			'		'
I _S	source current	T _{amb} = 25 °C		-	370	mA
ESD maxim	um rating			1	'	
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

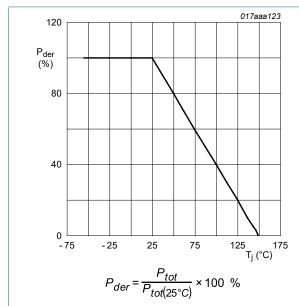


Fig. 1. Normalized total power dissipation as a function of junction temperature

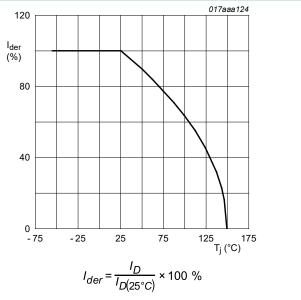


Fig. 2. Normalized continuous drain current as a function of junction temperature

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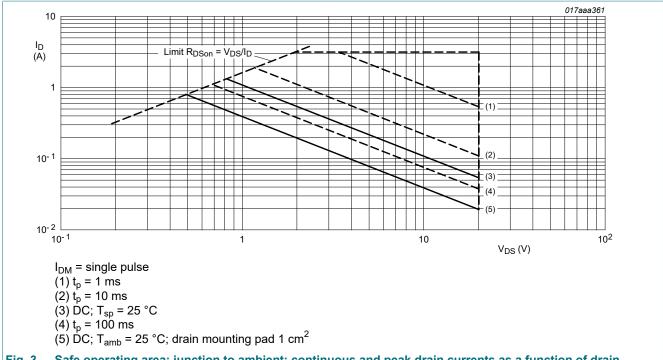


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	in free air	[1]	-	330	380	K/W
	junction to ambient		[2]	-	280	320	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W
Per device	'		,				
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

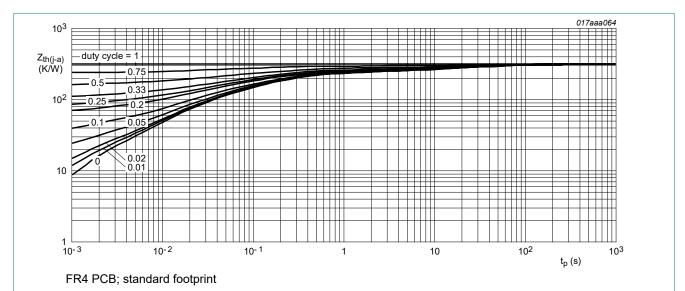


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

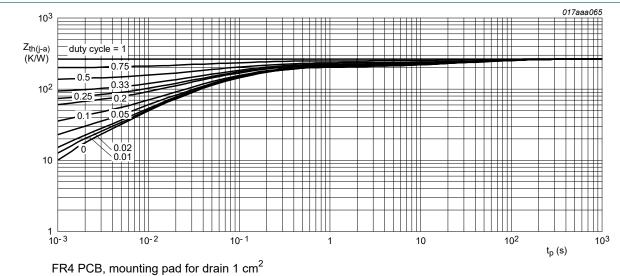


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
acteristics (per transistor)					
drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	20	-	-	V
gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	0.75	0.95	V
drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
	V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
	V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	500	nA
	$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	500	nA
drain-source on-state	V _{GS} = 4.5 V; I _D = 500 mA; T _j = 25 °C	-	290	380	mΩ
resistance	V _{GS} = 4.5 V; I _D = 500 mA; T _j = 150 °C	-	460	610	mΩ
	V _{GS} = 2.5 V; I _D = 400 mA; T _j = 25 °C	-	420	620	mΩ
	V _{GS} = 1.8 V; I _D = 100 mA; T _j = 25 °C	-	600	1100	mΩ
forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	1.6	-	S
naracteristics (per transist	or)				
total gate charge	V _{DS} = 10 V; I _D = 500 mA; V _{GS} = 4.5 V;	-	0.45	0.68	nC
gate-source charge	T _j = 25 °C	-	0.15	-	nC
gate-drain charge		-	0.15	-	nC
input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	55	83	pF
output capacitance	T _j = 25 °C	-	15	-	pF
reverse transfer capacitance		-	7	-	pF
turn-on delay time	$V_{DS} = 10 \text{ V}; R_L = 250 \Omega; V_{GS} = 4.5 \text{ V};$	-	6	12	ns
rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
turn-off delay time		-	86	172	ns
fall time		-	31	-	ns
in diode (per transistor)		'		,	
source-drain voltage	$I_S = 300 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	0.48	0.77	1.2	V
	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance forward transconductance maracteristics (per transist total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time in diode (per transistor)	drain-source threshold voltage gate-source threshold voltage drain leakage current $V_{DS} = 250 \mu A; V_{DS} = V_{CS}; T_j = 25 ^{\circ}C$ $V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 ^{\circ}C$ $V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 ^{\circ}C$ $V_{DS} = 20 V; V_{GS} = 0 V; T_j = 150 ^{\circ}C$ $V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 ^{\circ}C$ $V_{DS} = 20 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{DS} = 20 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{CS} = 8 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{CS} = 4.5 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{CS} = 4.5 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{CS} = 4.5 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{CS} = 4.5 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{CS} = 4.5 V; V_{DS} = 500 mA; T_j = 25 ^{\circ}C$ $V_{CS} = 4.5 V; V_{DS} = 500 mA; T_j = 25 ^{\circ}C$ $V_{CS} = 1.8 V; I_D = 500 mA; T_j = 25 ^{\circ}C$ $V_{CS} = 1.8 V; I_D = 100 mA; T_j = 25 ^{\circ}C$ $V_{CS} = 1.8 V; I_D = 100 mA; T_j = 25 ^{\circ}C$ $V_{CS} = 1.8 V; I_D = 200 mA; T_j = 25 ^{\circ}C$ $V_{CS} = 1.8 V; I_D = 200 mA; T_j = 25 ^{\circ}C$ $V_{CS} = 1.8 V; I_D = 100 mA; T_j = 25 ^{\circ}C$ $V_{CS} = 1.8 V; I_D = 100 mA; V_{CS} = 4.5 V; T_j = 25 ^{\circ}C$ $V_{CS} = 1.8 V; I_D = 100 mA; V_{CS} = 4.5 V; T_j = 25 ^{\circ}C$ $V_{CS} = 10 V; I_D = 100 V; I_D = 100 mA; V_{CS} = 1.5 V; T_J = 25 ^{\circ}C$ $V_{CS} = 1.0 V; I_D = 100 V; I_D = 10$			

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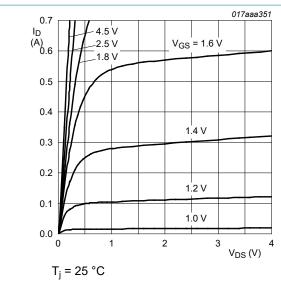
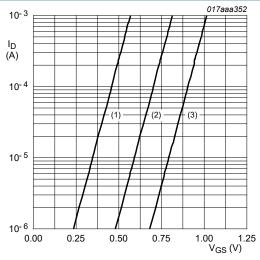


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



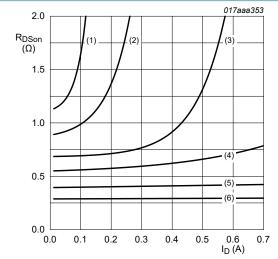
 $T_j = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



T_i = 25 °C

 $(1) V_{GS} = 1.3 V$

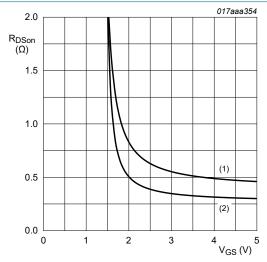
 $(2) V_{GS} = 1.4 V$

 $(3) V_{GS} = 1.6 V$

 $(4) V_{GS} = 1.8 V$

(5) $V_{GS} = 2.5 V$ (6) $V_{GS} = 4.5 V$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 400 \text{ mA}$ (1) $T_j = 150 \text{ °C}$

(2) $T_j = 25 \,^{\circ}\text{C}$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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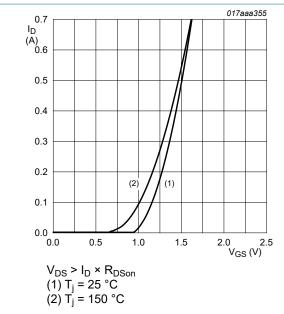
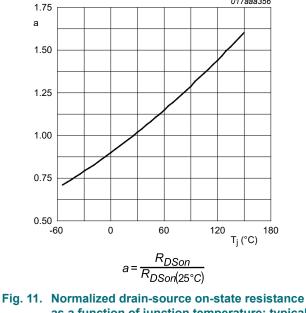
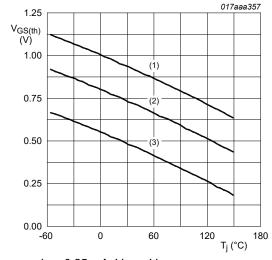


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



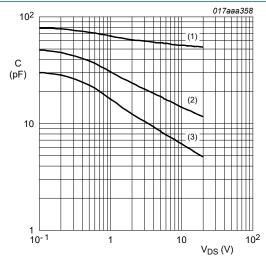
as a function of junction temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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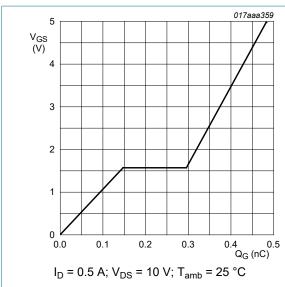


Fig. 14. Gate-source voltage as a function of gate charge; typical values

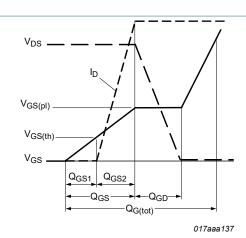
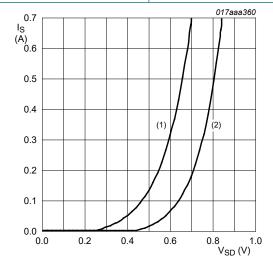


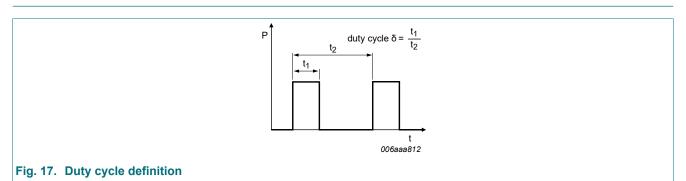
Fig. 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$ (2) $T_j = 25 \,^{\circ}C$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information



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12. Package outline

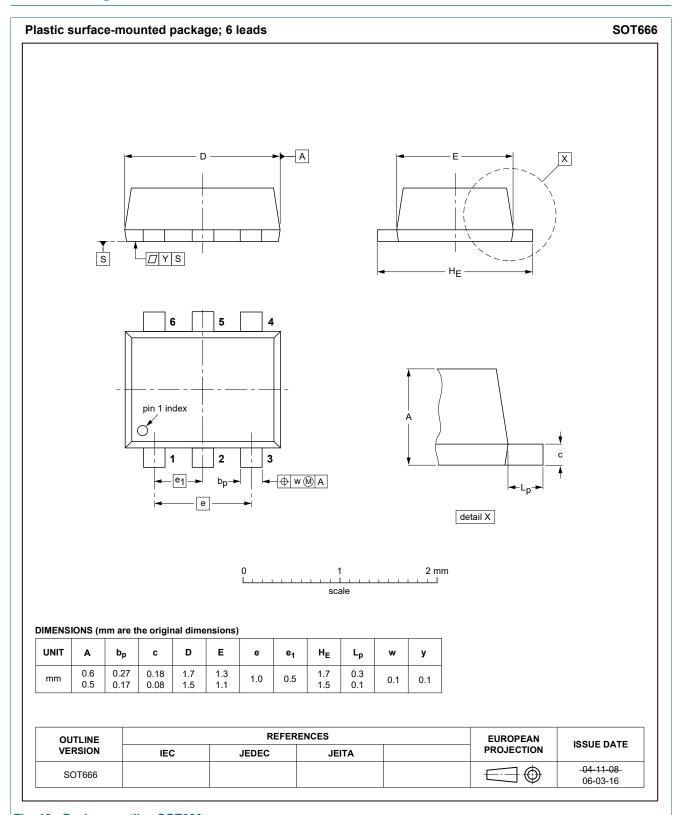
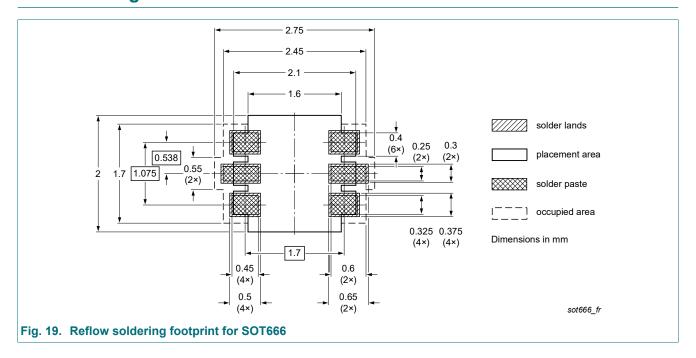


Fig. 18. Package outline SOT666

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMDT290UNE v.2	20221228	Product data sheet	-	PMDT290UNE v.1			
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia Legal texts have been adapted to the new company name where appropriate Product changed to non-automotive qualification 						
PMDT290UNE v.1	20110913	Product data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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